



SEMITOP®2

Thyristor and Diode
separated in the same
housing
SK 75 TAE

Target Data

Features

- Compact Design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DBC)
- Glass passivated thyristor chips
- Up to 1600V reverse voltage

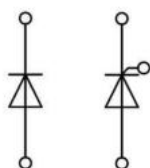
Typical Applications*

- UPS

1) REMARKS: V_T , $V_{T(TO)}$, V_F , V_{TO} = chip level value

| V_{RSM} V | V_{RRM} , V_{DRM} V | $I_T = 75$ A ($T_s = 80$ °C) |
|----------------|----------------------------|----------------------------------|
| 1300 | 1200 | SK75TAE12 |

| Characteristics $T_s = 25$ °C, unless otherwise specified | | | |
|---|--|--------------|-------|
| Symbol | Conditions | Values | Units |
| I_T | $T_s = 80$ °C | 75 | A |
| I_T | $T_s = 100$ °C | 50 | A |
| | | | A |
| I_{TSM}/I_{FSM} | $T_{vj} = 130$ °C; 10 ms | 1250 | A |
| I^2t | $T_{vj} = 130$ °C; half sine wave, 10 ms | 7810 | A²s |
| T_{stg} | | -40 ... +130 | °C |
| T_{solder} | terminals, 10 s | 260 | °C |
| Thyristor | | | |
| $(dv/dt)_{cr}$ | $T_{vj} = 125$ °C | 500 | V/μs |
| $(di/dt)_{cr}$ | $T_{vj} = 125$ °C; $f =$ Hz | 125 | A/μs |
| t_q | $T_{vj} = 130$ °C; typ. | 150 | μs |
| I_H | $T_{vj} = 25$ °C; typ. / max. | 250 / | mA |
| I_L | $T_{vj} = 25$ °C; $R_G =$; typ. / max. | 600 / | mA |
| V_T | $T_{vj} = 130$ °C; ($I_T = 110$ A); max. | 1,2 | V |
| $V_{T(TO)}$ | $T_{vj} = 130$ °C | max. 0,85 | V |
| r_T | $T_{vj} = 130$ °C | max. 4,4 | mΩ |
| I_{DD} ; I_{RD} | $T_{vj} =$ °C; $V_{DD} = V_{DRM}$; $V_{RD} = V_{RRM}$ | max. | mA |
| $R_{th(j-s)}$ | max. value | 0,6 | K/W |
| T_{vj} | | -40 ... +130 | °C |
| V_{GT} | $T_{vj} = 25$ °C; d.c. | 1,98 | V |
| I_{GT} | $T_{vj} = 25$ °C; d.c. | 100 | mA |
| V_{GD} | $T_{vj} = 130$ °C; d.c. | 0,25 | V |
| I_{GD} | $T_{vj} = 115$ °C; d.c. | 6 | mA |
| Diode | | | |
| V_F | $T_{vj} = 125$ °C; ($I_F = 100$ A); max. | 1,1 | V |
| $V_{(TO)}$ | $T_{vj} = 125$ °C | 0,83 | V |
| r_T | $T_{vj} = 125$ °C | 1,6 | mΩ |
| I_{RD} | $T_{vj} =$ °C; $V_{RD} = V_{RRM}$ | | mA |
| $R_{th(j-s)}$ | max. value | 0,62 | K/W |
| T_{vj} | | -40 ... +150 | °C |
| Mechanical data | | | |
| V_{isol} | a.c. 50Hz; r.m.s.; 1s (1min) | 2500 (3000) | V |
| M_1 | mounting torque | 2 | Nm |
| w | | 19 | g |
| Case | SEMITOP®2 | T 82 | |



TAE

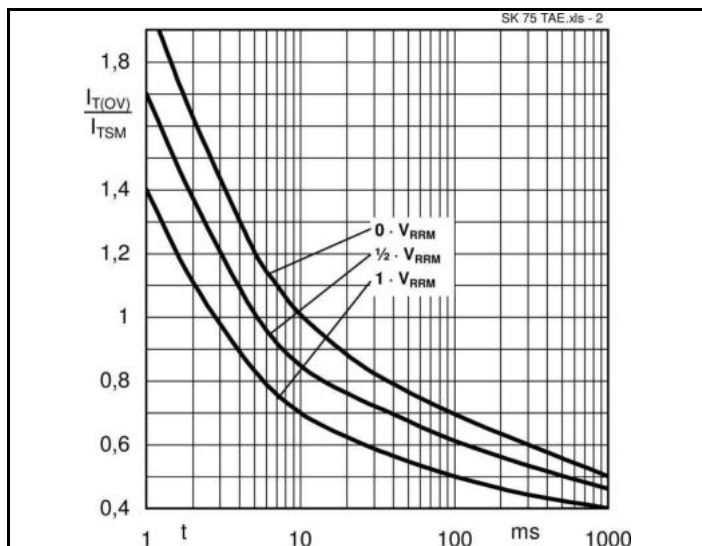


Fig.2 Surge overload current vs. time

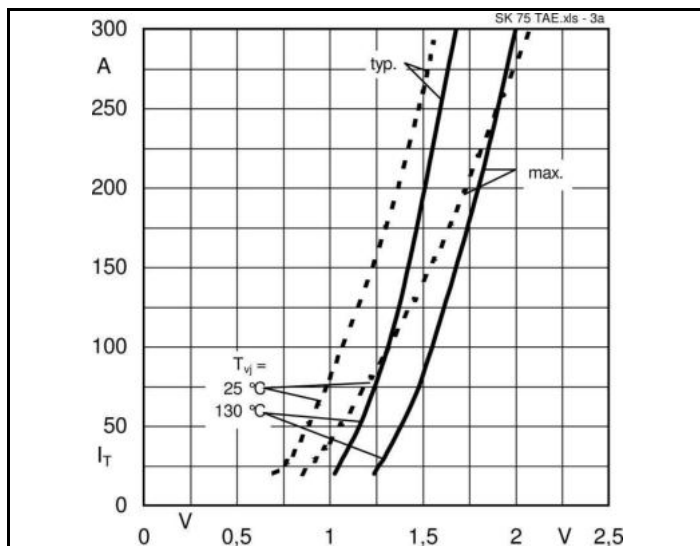


Fig.3a Thyristor forward characteristic

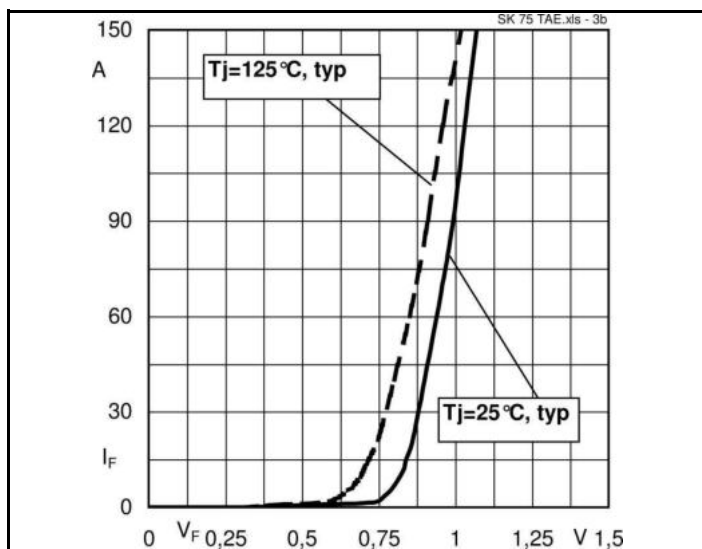


Fig.3b Diode forward characteristic

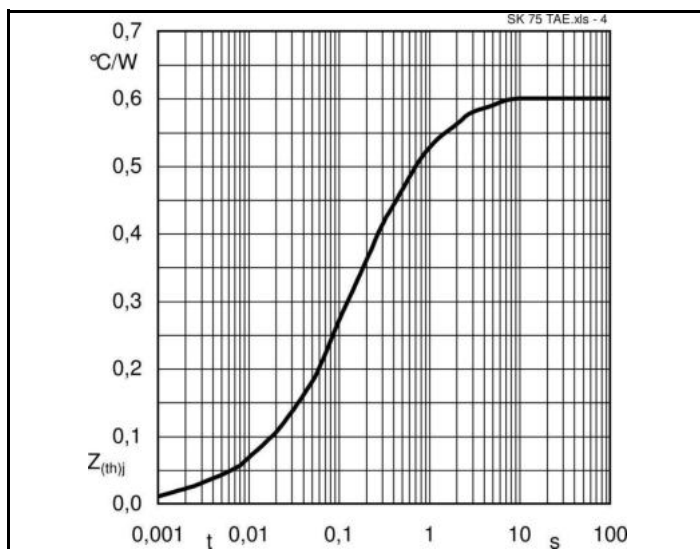


Fig.4 Transient thermal impedance of Thyristor

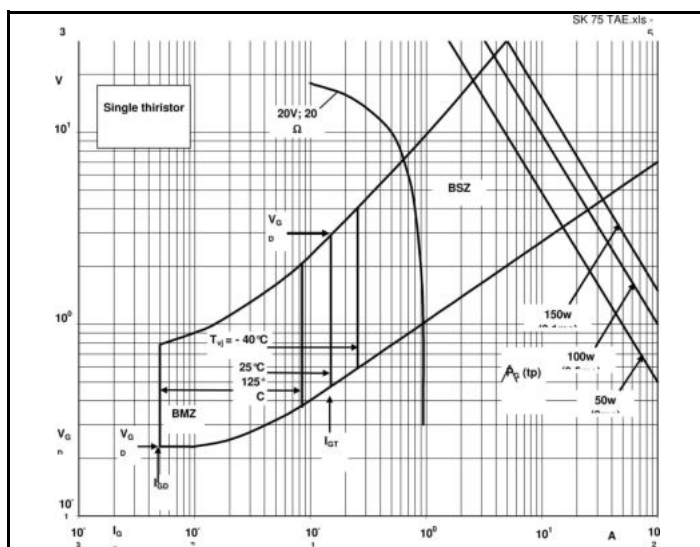
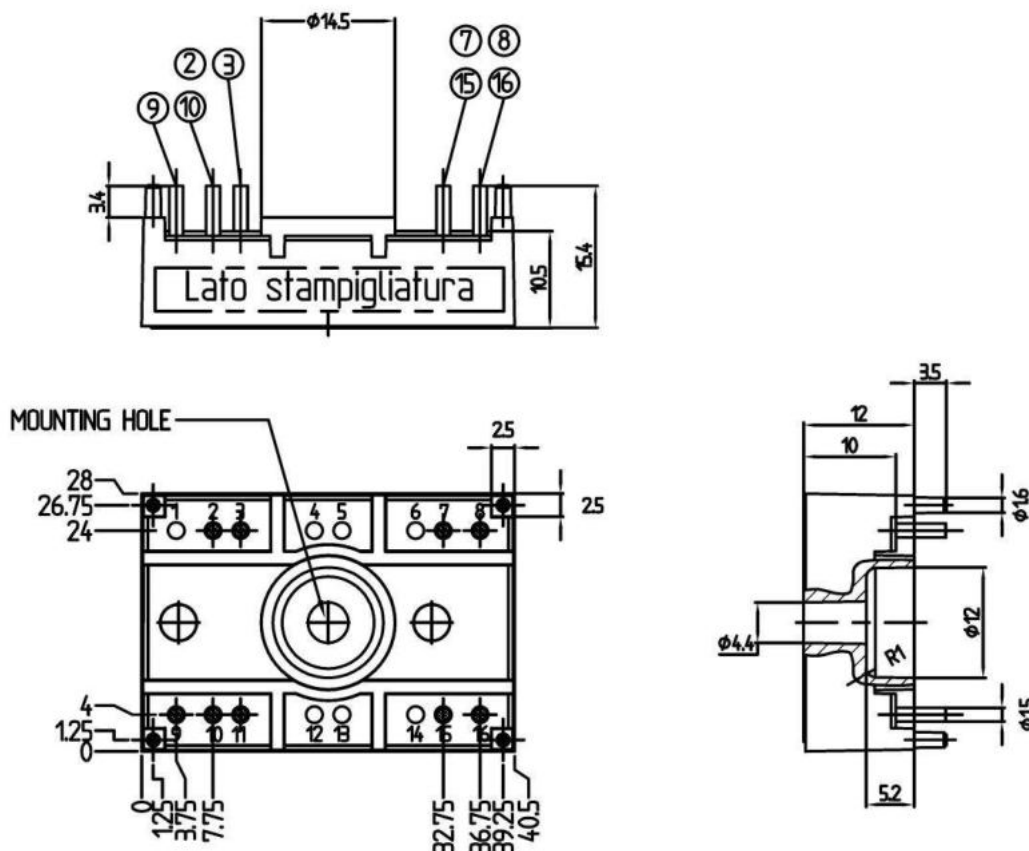


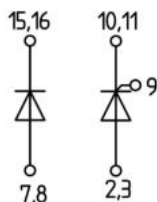
Fig.5 Gate trigger characteristic

Dimensions in mm



SUGGESTED HOLEDIAMETER FOR THE SOLDER PINS AND THE MOUNTING PINS IN THE PCB: 2 mm

Case T82 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)



T82

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.